

TOSHIBA**2SA1358**

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1358

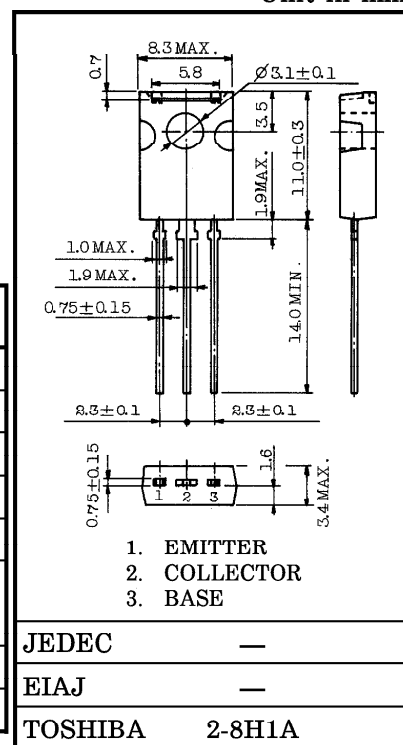
AUDIO FREQUENCY POWER AMPLIFIER APPLICATIONS.

Unit in mm

- Complementary to 2SC3421
- Suitable for Driver of 60 to 80 Watts.
- High Breakdown Voltage.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-120	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1	A
Base Current	I_B	-100	mA
Collector Power Dissipation	$T_a = 25^\circ\text{C}$ $T_c = 25^\circ\text{C}$ P_C	1.5	W
		10	
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



Weight : 0.82g

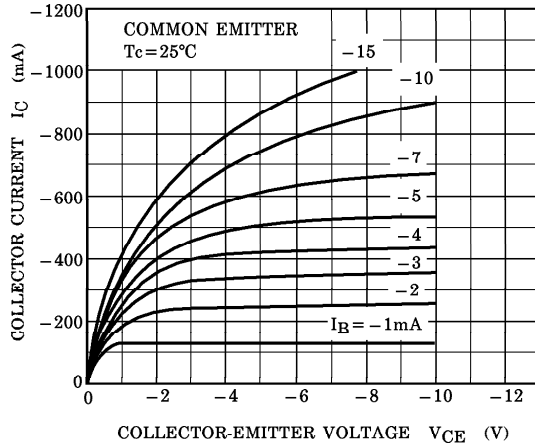
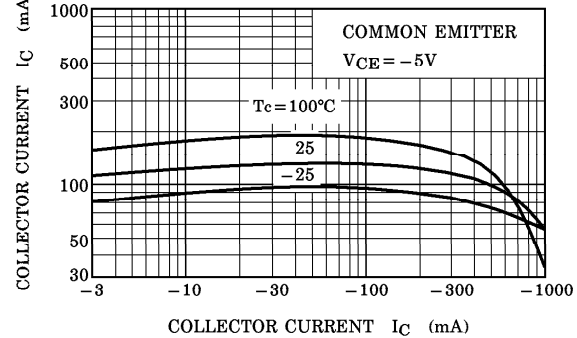
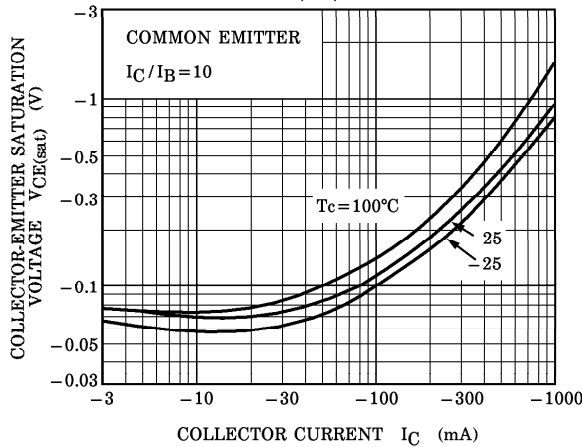
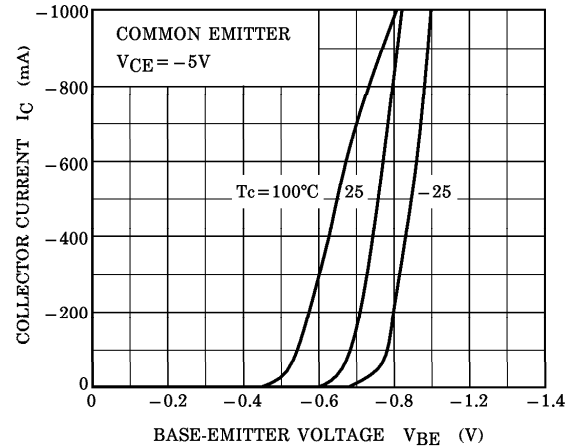
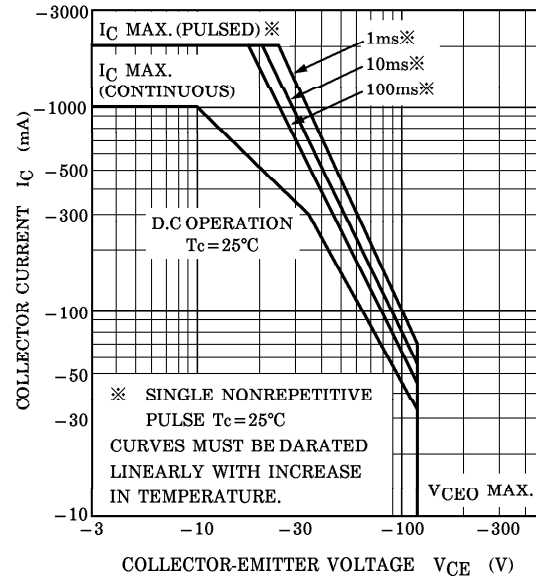
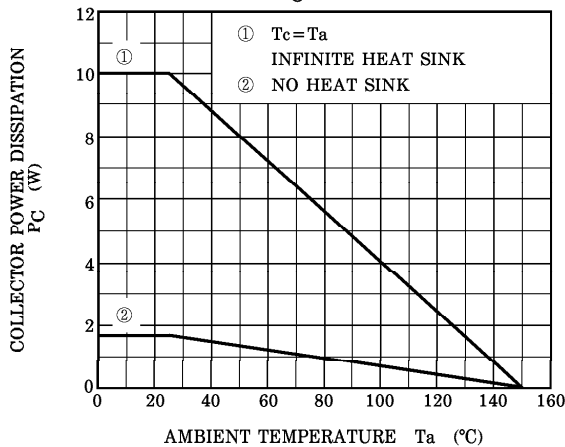
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -120\text{V}, I_E = 0$	—	—	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$	—	—	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-120	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1\text{mA}, I_C = 0$	-5	—	—	V
DC Current Gain	h_{FE} (Note)	$V_{CE} = -5\text{V}, I_C = -100\text{mA}$	80	—	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$	—	-0.40	-1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5\text{V}, I_C = -500\text{mA}$	—	-0.77	-1.0	V
Transition Frequency	f_T	$V_{CE} = -5\text{V}, I_C = -100\text{mA}$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$	—	30	—	pF

Note : h_{FE} Classification O : 80~160, Y : 120~240

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TOSHIBA**2SA1358** **$I_C - V_{CE}$**  **$h_{FE} - I_C$**  **$V_{CE(sat)} - I_C$**  **$I_C - V_{BE}$** **SAFE OPERATING AREA** **$P_C - T_a$** 

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